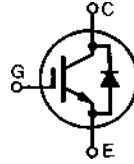


Preliminary data

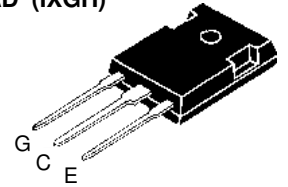
# Low $V_{CE(sat)}$ High speed IGBT with Diode

**IXGH25N100U1**  
**IXGH25N100AU1**

$V_{CES}$	$I_{C25}$	$V_{CE(sat)}$
1000 V	50 A	3.5 V
1000 V	50 A	4.0 V



TO-247 AD (IXGH)



G = Gate                      C = Collector  
E = Emitter                    TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1000	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1\text{ M}\Omega$	1000	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	50	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	25	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	100	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15\text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 33\ \Omega$ Clamped inductive load, $L = 100\ \mu\text{H}$	$I_{CM} = 50$ @ $0.8 V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	200	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque (M3)	1.13/10	Nm/lb.in.
<b>Weight</b>		TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

## Features

- International standard package JEDEC TO-247 AD
- IGBT and anti-parallel FRED in one package
- 2nd generation HDMOS™ process
- Low  $V_{CE(sat)}$ 
  - for minimum on-state conduction losses
- MOS Gate turn-on
  - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
  - soft recovery with low  $I_{RM}$

## Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

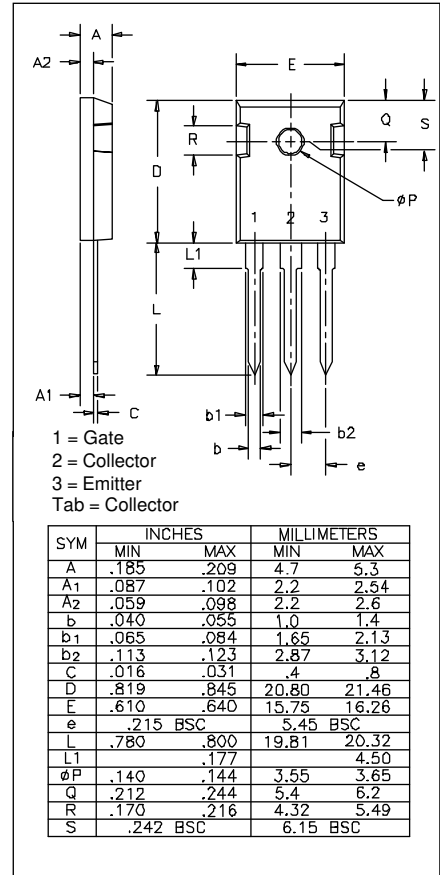
## Advantages

- Saves space (two devices in one package)
- Easy to mount (isolated mounting screw hole)
- Reduces assembly time and cost

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 4.5\text{ mA}$ , $V_{GE} = 0\text{ V}$	1000		V
$V_{GE(th)}$	$I_C = 500\ \mu\text{A}$ , $V_{CE} = V_{GE}$	2.5		5.5 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$			500 $\mu\text{A}$ 8 mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$			25N100U1: 3.5 V 25N100AU1: 4.0 V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_{C90}$ ; $V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	8	15	S
$C_{ies}$ $C_{oes}$ $C_{res}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		2750	pF
			270	pF
			50	pF
$Q_g$ $Q_{ge}$ $Q_{gc}$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.5 V_{CES}$		130	nC
			25	nC
			55	nC
$t_{d(on)}$ $t_{ri}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $L = 300\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = R_{off} = 33\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		100	ns
			200	ns
			500	ns
		25N100AU1	500	ns
		25N100AU1	5	mJ
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $L = 300\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = R_{off} = 33\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		100	ns
			250	ns
			3.5	mJ
		25N100U1	720	1000 ns
		25N100AU1	950	3000 ns
		25N100AU1	800	ns
		25N100AU1	10	mJ
	25N100AU1	6	mJ	
$R_{thJC}$ $R_{thCK}$			0.62 K/W	
		0.25	K/W	

### TO-247 AD Outline



Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = I_{C90}$ , $V_{GE} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			2.5 V
$I_{RM}$ $t_{tr}$	$I_F = I_{C90}$ , $V_{GE} = 0\text{ V}$ , $-di_F/dt = 240\text{ A}/\mu\text{s}$ $V_R = 540\text{ V}$		16	18 A
		$T_J = 125^\circ\text{C}$	120	ns
	$I_F = 1\text{ A}$ ; $-di/dt = 100\text{ A}/\mu\text{s}$ ; $V_R = 30\text{ V}$	$T_J = 25^\circ\text{C}$	35	50 ns
$R_{thJC}$				1 K/W

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

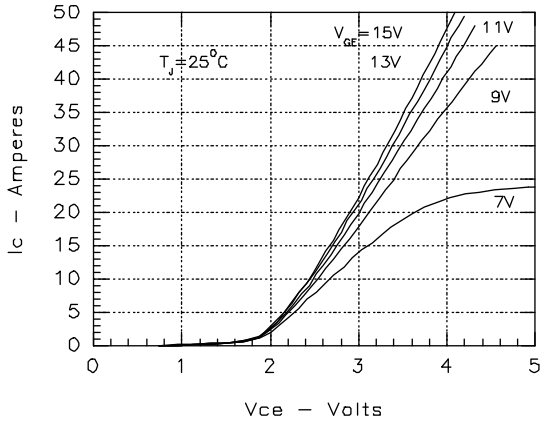
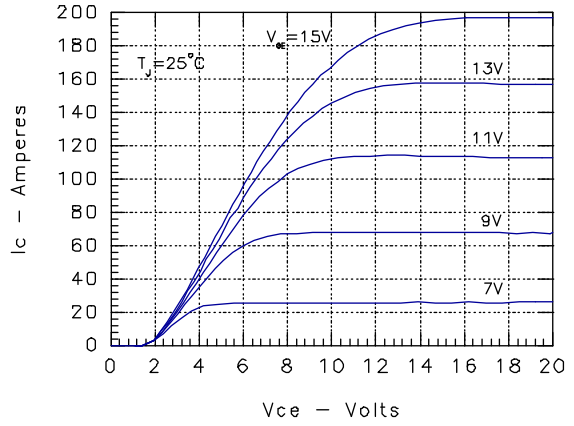
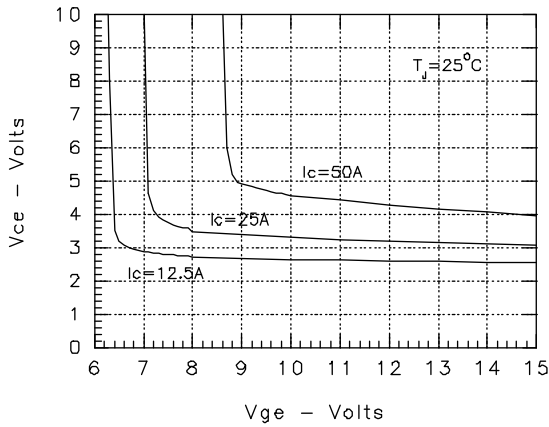
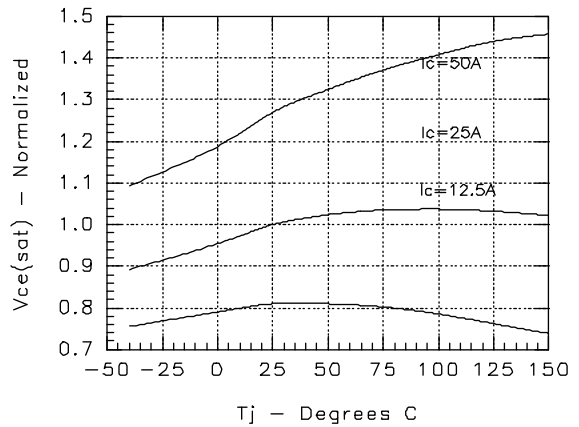
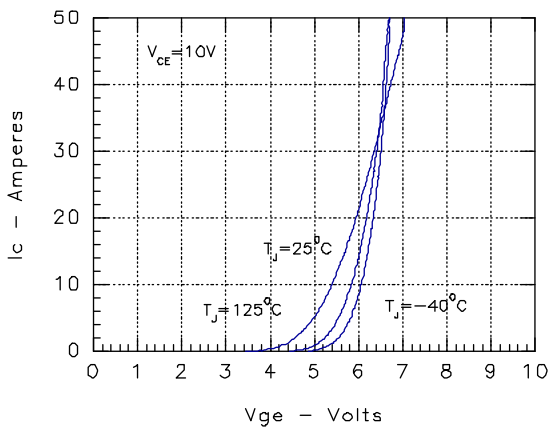
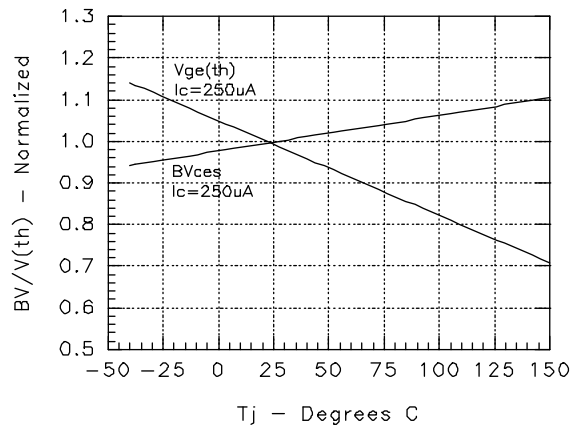
**Fig. 1. Saturation Characteristics**

**Fig. 2. Output Characteristics**

**Fig. 3. Collector-Emitter Voltage vs. Gate-Emitter Voltage**

**Fig. 4. Temperature Dependence of Output Saturation Voltage**

**Fig. 5. Input Admittance**

**Fig. 6. Temperature Dependence Breakdown and Threshold Voltage**


Fig. 7. Gate Charge

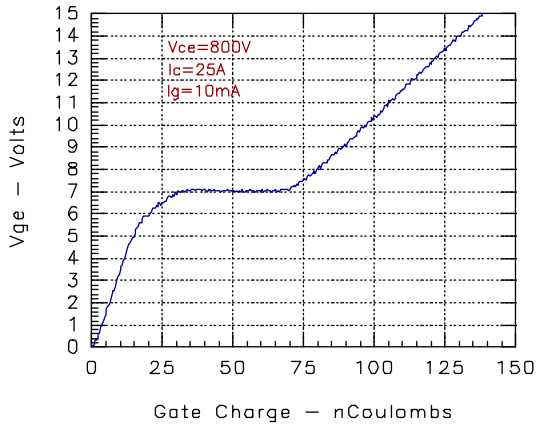


Fig. 8. Turn-Off Safe Operating Area

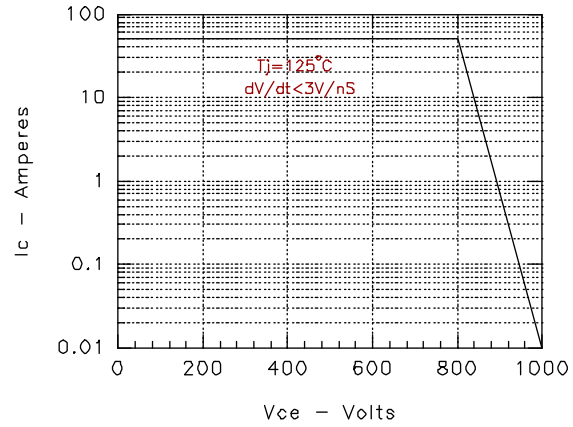


Fig. 9. Capacitance Curves

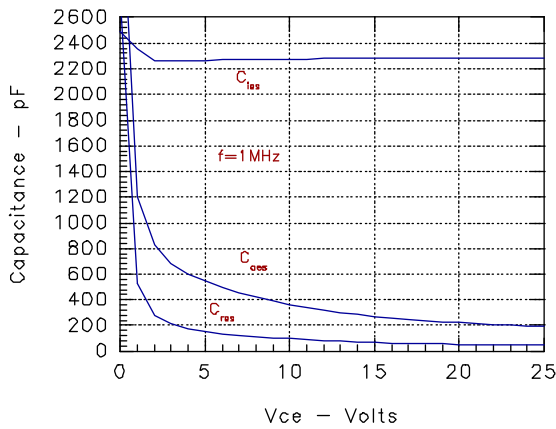
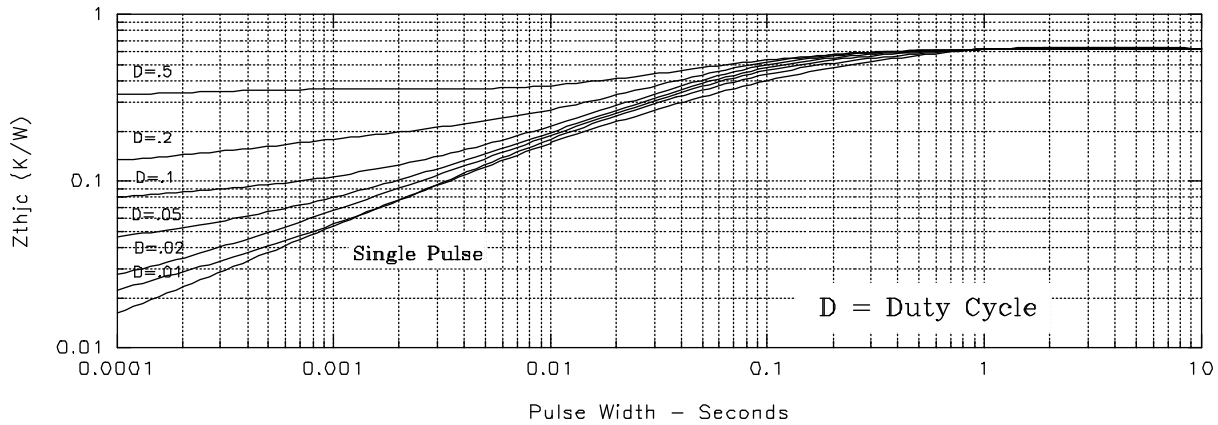


Fig. 10. Transient Thermal Impedance



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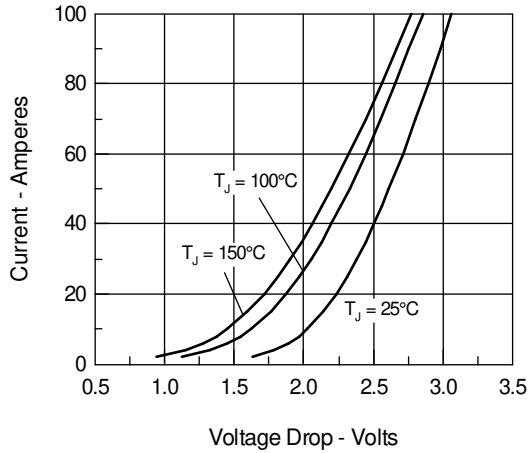
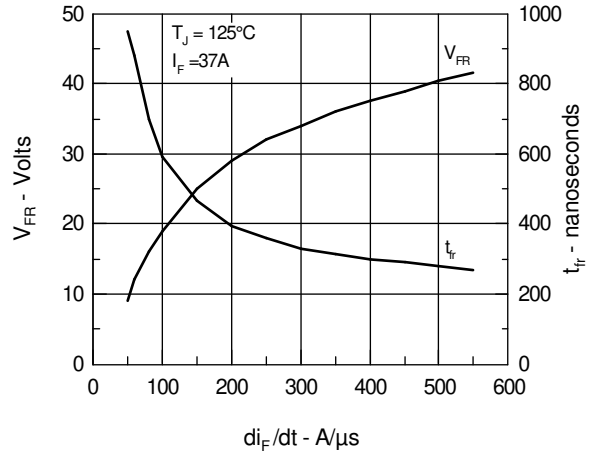
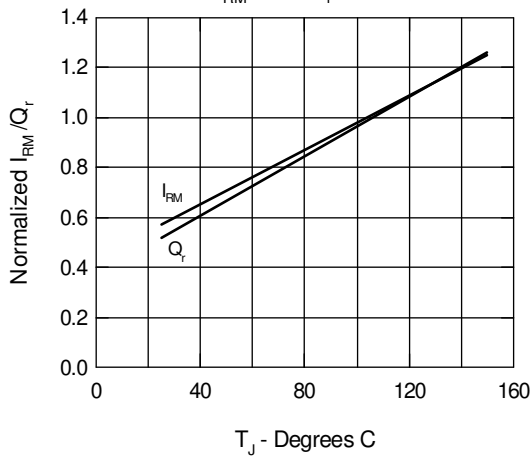
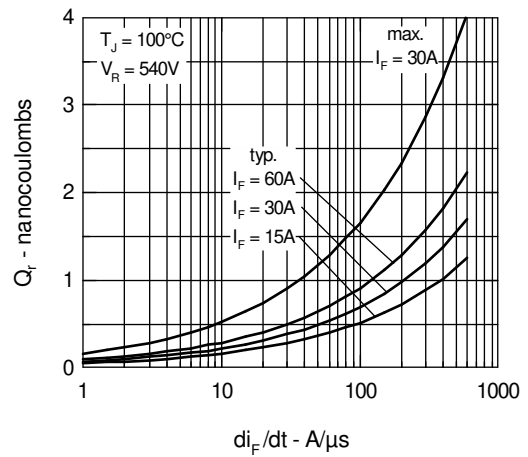
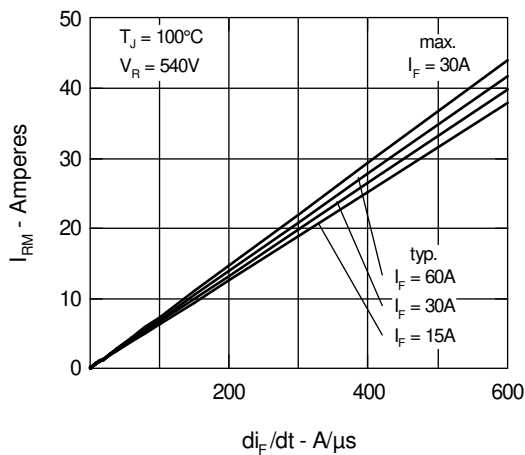
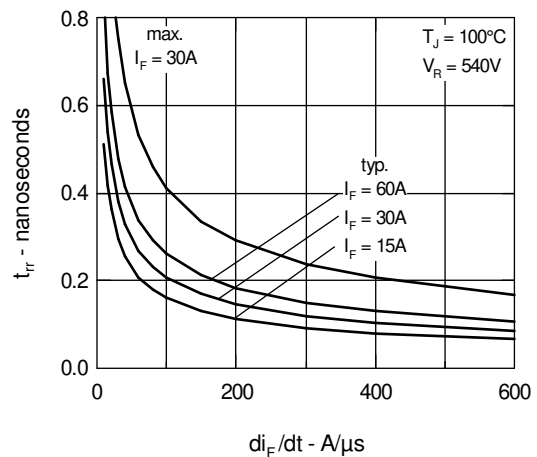
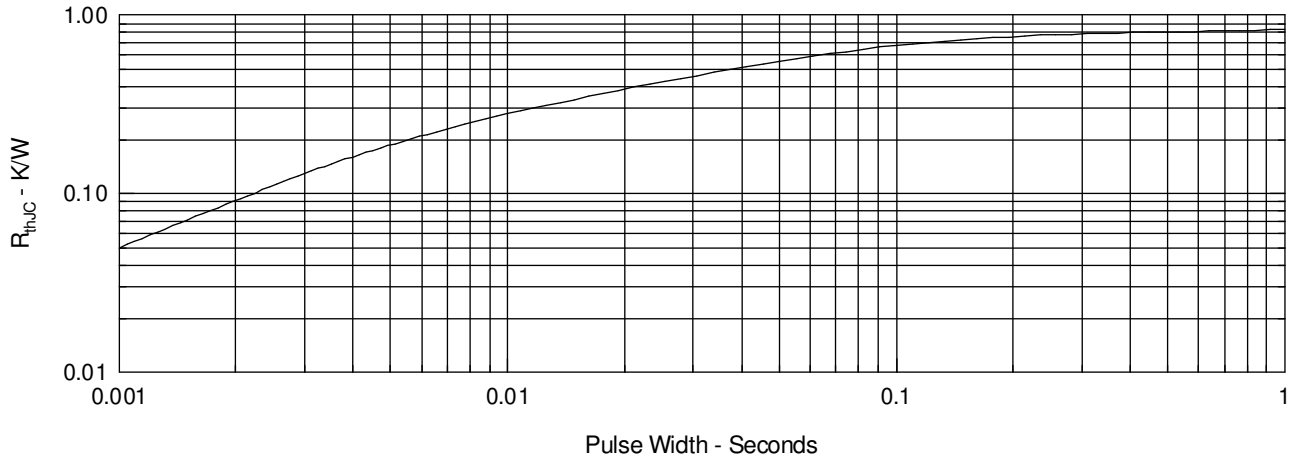
**Fig.11 Maximum Forward Voltage Drop**

**Fig.12 Peak Forward Voltage  $V_{FR}$  and Forward Recovery Time  $t_{FR}$** 

**Fig.13 Junction Temperature Dependence of  $I_{RM}$  and  $Q_r$** 

**Fig.14 Reverse Recovery Charge  $Q_r$** 

**Fig.15 Peak Reverse Recovery Current  $I_{RM}$** 

**Fig.16 Reverse Recovery Time  $t_{rr}$** 


Fig.17 Diode Transient Thermal resistance junction to case



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